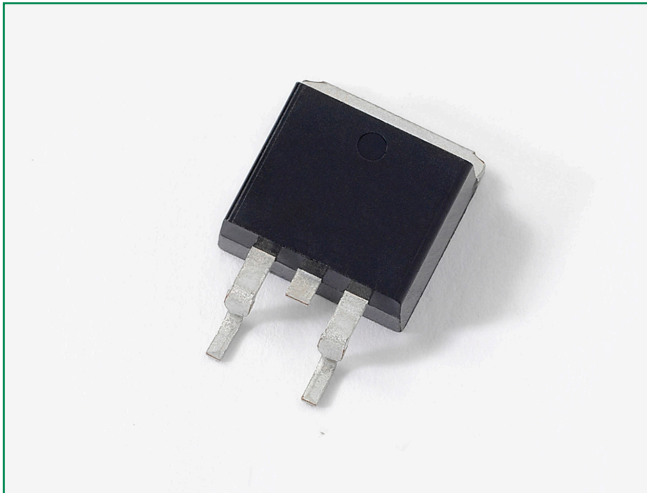


NGB8206AN - 20 A, 350 V, N-Channel Ignition IGBT, D²PAK



20 Amps, 350 Volts
 $V_{CE(on)} \leq 1.3 V @$
 $I_C = 10A, V_{GE} \geq 4.5 V$

Maximum Ratings ($T_J = 25^\circ C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	390	V
Collector–Gate Voltage	V_{CER}	390	V
Gate–Emitter Voltage	V_{GE}	± 15	V
Collector Current–Continuous @ $T_c = 25^\circ C$ – Pulsed	I_C	20 50	A_{DC} A_{AC}
Continuous Gate Current	I_G	1.0	mA
Transient Gate Current ($t \leq 2$ ms, $f \leq 100$ Hz)	I_G	20	mA
ESD (Charged–Device Model)	ESD	2.0	kV
ESD (Human Body Model) $R = 1500 \Omega$, $C = 100$ pF	ESD	8.0	kV
ESD (Machine Model) $R = 0 \Omega$, $C = 200$ pF	ESD	500	V
Total Power Dissipation @ $T_c = 25^\circ C$ Derate above $25^\circ C$	P_D	150 1.0	Watts W/ $^\circ C$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to $+175$	$^\circ C$

Description

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features monolithic circuitry integrating ESD and Over–Voltage clamped protection for use in inductive coil drivers applications. Primary uses include Ignition, Direct Fuel Injection, or wherever high voltage and high current switching is required.

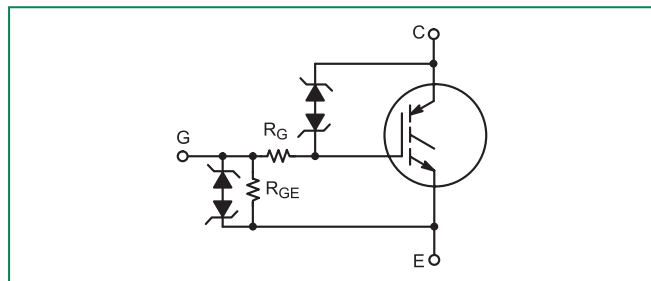
Features

- Ideal for Coil–on–Plug and Driver–on–Coil Applications
- Gate–Emitter ESD Protection
- Temperature Compensated Gate–Collector Voltage Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- Low Threshold Voltage for Interfacing Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability
- These are Pb–Free Devices

Applications

- Ignition Systems

Functional Diagram



Additional Information



Datasheet



Resources



Samples

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Unclamped Collector–To–Emitter Avalanche Characteristics ($-55^{\circ} \leq T_J \leq 175^{\circ}\text{C}$)

	Symbol	Value	Unit
Single Pulse Collector–to–Emitter Avalanche Energy			
$V_{CC} = 50\text{ V}, V_{GE} = 5.0\text{ V}, P_k I_L = 16.7\text{ A}, R_G = 1000\ \Omega, L = 1.8\text{ mH}, \text{Starting } T_J = 25^{\circ}\text{C}$	E_{AS}	250	mJ
$V_{CC} = 50\text{ V}, V_{GE} = 5.0\text{ V}, P_k I_L = 14.9\text{ A}, R_G = 1000\ \Omega, L = 1.8\text{ mH}, \text{Starting } T_J = 150^{\circ}\text{C}$		200	
$V_{CC} = 50\text{ V}, V_{GE} = 5.0\text{ V}, P_k I_L = 14.1\text{ A}, R_G = 1000\ \Omega, L = 1.8\text{ mH}, \text{Starting } T_J = 175^{\circ}\text{C}$		180	
Reverse Avalanche Energy			
$V_{CC} = 100\text{ V}, V_{GE} = 20\text{ V}, P_k I_L = 25.8\text{ A}, L = 6.0\text{ mH}, \text{Starting } T_J = 25^{\circ}\text{C}$	$E_{AS(R)}$	2000	mJ

1. When surface mounted to an FR4 board using the minimum recommended pad size.

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	62.5	$^{\circ}\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T_L	275	$^{\circ}\text{C}$

Electrical Characteristics - OFF

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
Collector–Emitter Clamp Voltage	BV_{CES}	$I_C = 2.0 \text{ mA}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	325	350	375	V
		$I_C = 10 \text{ mA}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	340	365	390	
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 15 \text{ V},$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$	–	0.1	1.0	μA
			$T_J = 25^\circ\text{C}$	0.5	1.5	10	
			$T_J = 175^\circ\text{C}$	1.0	25	100*	
Reverse Collector–Emitter Clamp Voltage	$BV_{CES(R)}$	$I_C = -75 \text{ mA}$	$T_J = 25^\circ\text{C}$	30	35	39	V
			$T_J = 175^\circ\text{C}$	32	37	42	
			$T_J = -40^\circ\text{C}$	29	32	37	
Reverse Collector–Emitter Leakage Current	$I_{CES(R)}$	$V_{CE} = -24 \text{ V}$	$T_J = 25^\circ\text{C}$	0.05	0.25	1.0	mA
			$T_J = 175^\circ\text{C}$	1.0	12.5	25	
			$T_J = -40^\circ\text{C}$	0.005	0.03	0.25	
Gate–Emitter Clamp Voltage	BV_{GES}	$I_G = \pm 5.0 \text{ mA}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	12	12.5	14	V
Gate–Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 5.0 \text{ V}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	200	300	350*	μA
Gate Resistor	R_G	–	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	–	–	–	Ω
Gate Emitter Resistor	R_{GE}	–	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	14.25	16	25	k Ω

Electrical Characteristics - ON (Note 3)

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
Gate Threshold Voltage	$V_{GE(th)}$	$I_C = 1.0 \text{ mA},$ $V_{GE} = V_{CE}$	$T_J = 25^\circ\text{C}$	1.5	1.8	2.1	V
			$T_J = 175^\circ\text{C}$	0.7	1.0	1.3	
			$T_J = -40^\circ\text{C}$	1.7	2.0	2.3*	
Threshold Temperature Coefficient (Negative)	–	–	–	3.8	4.6	6.0	mV/ $^\circ\text{C}$

*Maximum Value of Characteristic across Temperature Range.

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

Electrical Characteristics - ON (Note 4)

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
Collector-to-Emitter On-Voltage	$V_{CE(on)}$	$I_C = 6.5\text{ A},$ $V_{GE} = 3.7\text{ V}$	$T_J = 25^\circ\text{C}$	0.95	1.15	1.35	V
			$T_J = 175^\circ\text{C}$	0.70	0.95	1.15	
			$T_J = -40^\circ\text{C}$	1.0	1.30	1.40	
		$I_C = 9.0\text{ A},$ $V_{GE} = 3.9\text{ V}$	$T_J = 25^\circ\text{C}$	0.95	1.25	1.45	
			$T_J = 175^\circ\text{C}$	0.8	1.05	1.25	
			$T_J = -40^\circ\text{C}$	1.1	1.4	1.50	
		$I_C = 7.5\text{ A},$ $V_{GE} = 4.5\text{ V}$	$T_J = 25^\circ\text{C}$	0.85	1.15	1.4	
			$T_J = 175^\circ\text{C}$	0.7	0.95	1.2	
			$T_J = -40^\circ\text{C}$	1.0	1.3	1.6*	
		$I_C = 10\text{ A},$ $V_{GE} = 4.5\text{ V}$	$T_J = 25^\circ\text{C}$	0.9	1.2	1.6	
			$T_J = 175^\circ\text{C}$	0.8	1.05	1.4	
			$T_J = -40^\circ\text{C}$	1.0	1.2	1.7*	
		$I_C = 15\text{ A},$ $V_{GE} = 4.5\text{ V}$	$T_J = 25^\circ\text{C}$	1.0	1.3	1.7	
			$T_J = 175^\circ\text{C}$	1.0	1.3	1.55	
			$T_J = -40^\circ\text{C}$	1.1	1.35	1.8*	
$I_C = 20\text{ A},$ $V_{GE} = 4.5\text{ V}$	$T_J = 25^\circ\text{C}$	1.3	1.6	1.9			
	$T_J = 175^\circ\text{C}$	1.2	1.5	1.8			
	$T_J = -40^\circ\text{C}$	1.4	1.75	2.0*			
Forward Transconductance	gfs	$V_{CE} = 5.0\text{ V},$ $I_C = 6.0\text{ A}$	$T_J = 25^\circ\text{C}$	10	18	25	Mhos

*Maximum Value of Characteristic across Temperature Range.

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

Dynamic Characteristics

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
Input Capacitance	C_{ISS}	$V_{CE} = 25\text{ V}$ $f = 10\text{ kHz}$	$T_J = 25^\circ\text{C}$	1100	1300	1500	pF
Output Capacitance	C_{OSS}			70	80	90	
Transfer Capacitance	C_{RSS}			18	20	22	

Switching Characteristics

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit	
Turn-Off Delay Time (Resistive)	$t_{d(off)}$	$V_{CC} = 300\text{ V}$, $I_C = 9\text{ A}$, $R_G = 1.0\text{ k}\Omega$, $R_L = 33\ \Omega$, $V_{GE} = 5.0\text{ V}$	$T_J = 25^\circ\text{C}$	6.0	8.0	10	μSec	
			$T_J = 175^\circ\text{C}$	6.0	8.0	10		
Fall Time (Resistive)	t_f		$T_J = 25^\circ\text{C}$	4.0	6.0	8.0		
			$T_J = 175^\circ\text{C}$	8.0	10.5	14		
Turn-Off Delay Time (Inductive)	$t_{d(off)}$		$V_{CC} = 300\text{ V}$, $I_C = 9\text{ A}$, $R_G = 1.0\text{ k}\Omega$, $L = 300\ \mu\text{H}$, $V_{GE} = 5.0\text{ V}$	$T_J = 25^\circ\text{C}$	3.0	5.0		7.0
				$T_J = 175^\circ\text{C}$	5.0	7.0		9.0
Fall Time (Inductive)	t_f	$T_J = 25^\circ\text{C}$		1.5	3.0	4.5		
		$T_J = 175^\circ\text{C}$		5.0	7.0	10		
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 14\text{ V}$, $I_C = 9.0\text{ A}$, $R_G = 1.0\text{ k}\Omega$, $R_L = 1.5\ \Omega$, $V_{GE} = 5.0\text{ V}$		$T_J = 25^\circ\text{C}$	1.0	1.5	2.0	
				$T_J = 175^\circ\text{C}$	1.0	1.5	2.0	
Rise Time	t_r		$T_J = 25^\circ\text{C}$	4.0	6.0	8.0		
			$T_J = 175^\circ\text{C}$	3.0	5.0	7.0		

 2. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

*Maximum Value of Characteristic across Temperature Range.

Ratings and Characteristic Curves

Figure 1. Self Clamped Inductive Switching

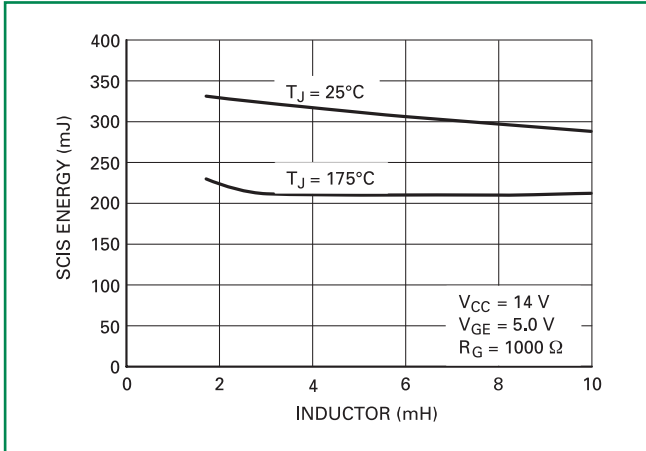


Figure 2. Open Secondary Avalanche Current vs. Temperature

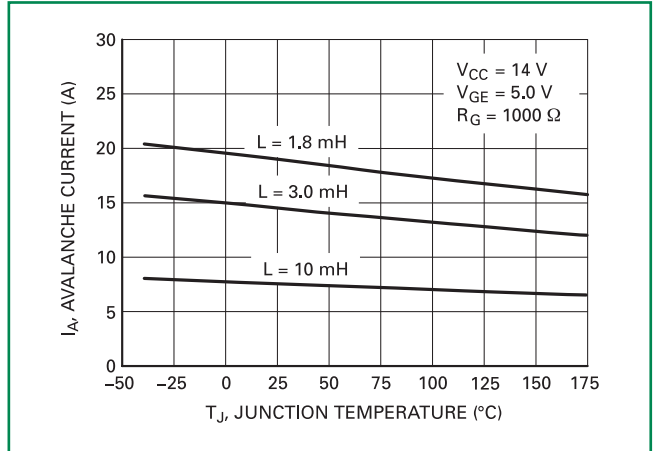


Figure 3. Collector-to-Emitter Voltage vs. Junction Temperature

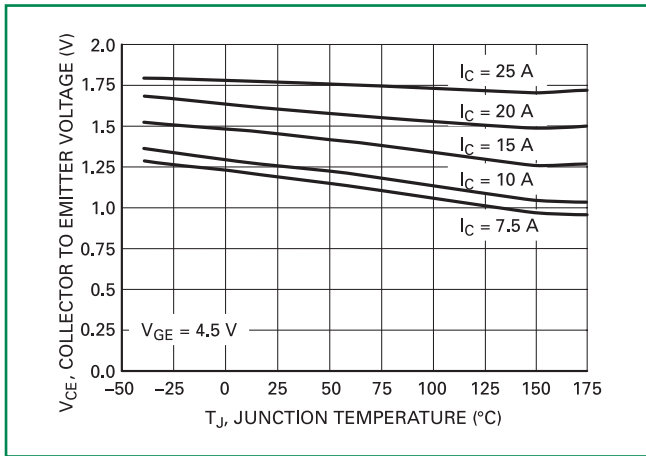


Figure 4. Collector Current vs. Collector-to-Emitter Voltage

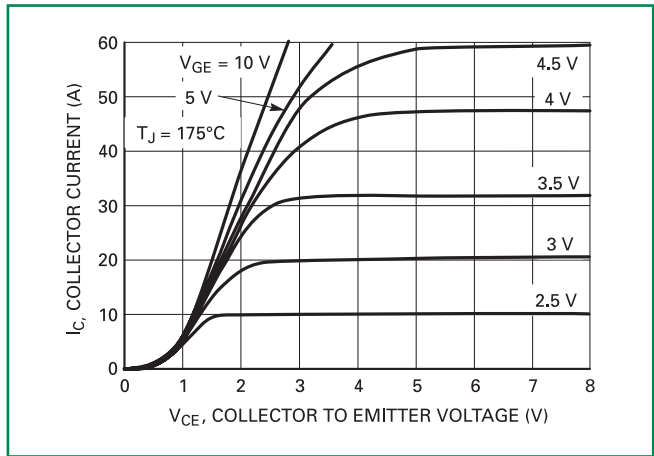


Figure 5. Collector Current vs. Collector-to-Emitter Voltage

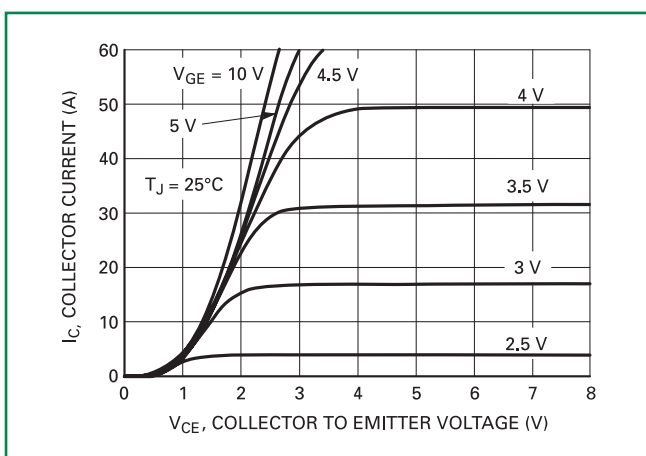


Figure 6. Collector Current vs. Collector-to-Emitter Voltage

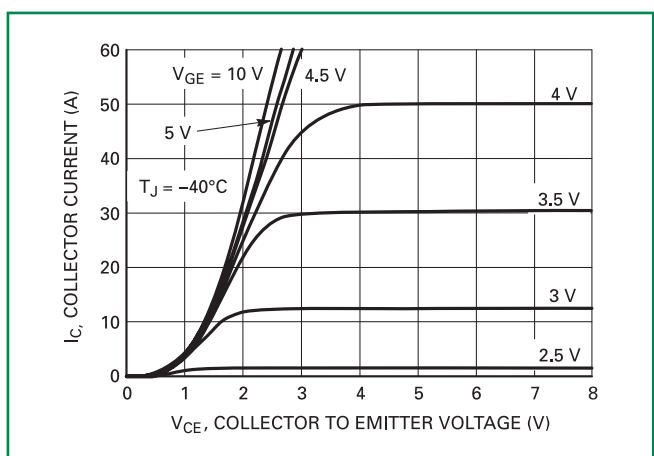


Figure 7. Transfer Characteristics

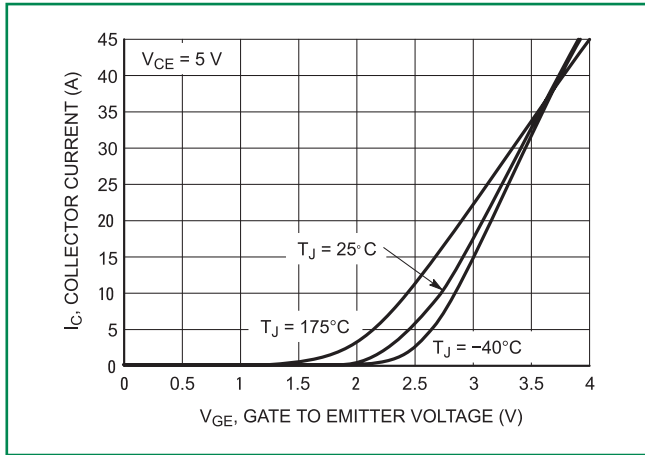


Figure 8. Collector-to-Emitter Leakage Current vs. Temperature

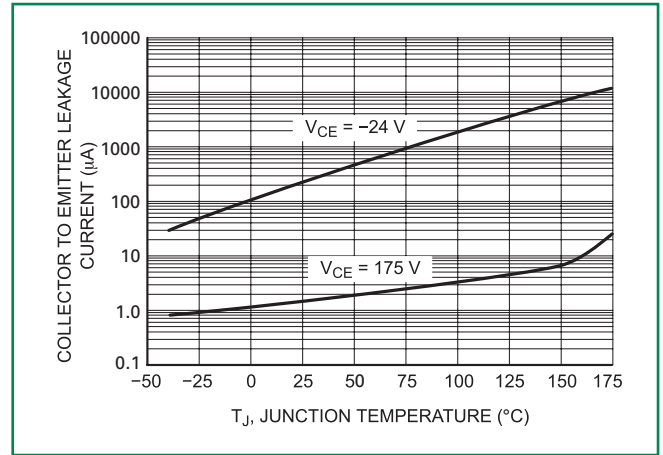


Figure 9. Gate Threshold Voltage vs. Temperature

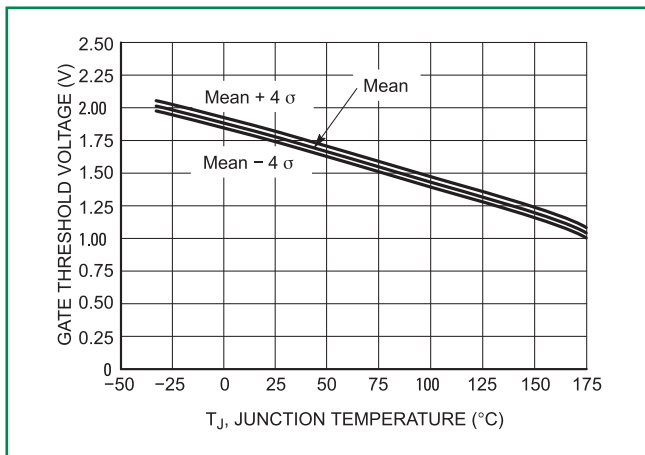


Figure 10. Capacitance vs. Collector-to-Emitter Voltage

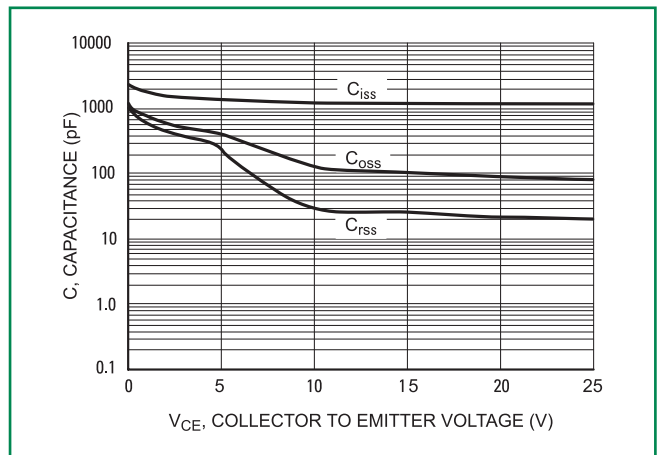


Figure 11. Resistive Switching Fall Time vs. Temperature

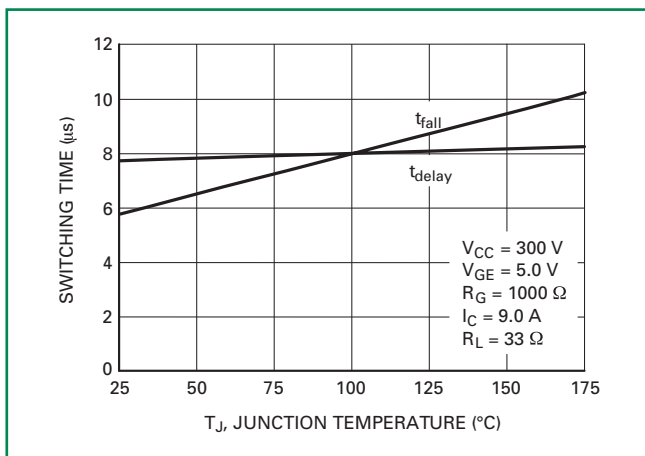


Figure 12. Inductive Switching Fall Time vs. Temperature

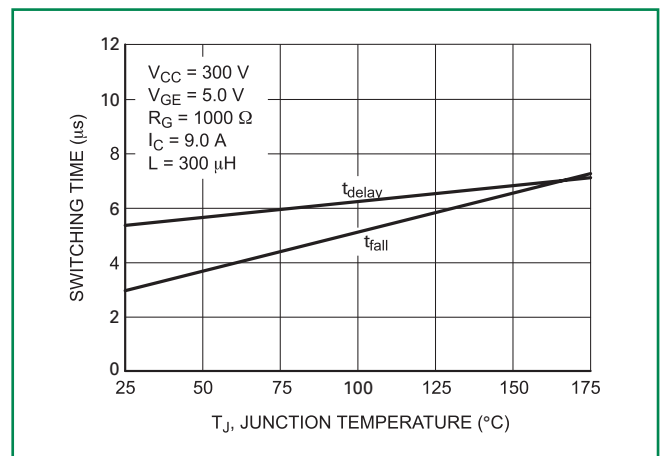
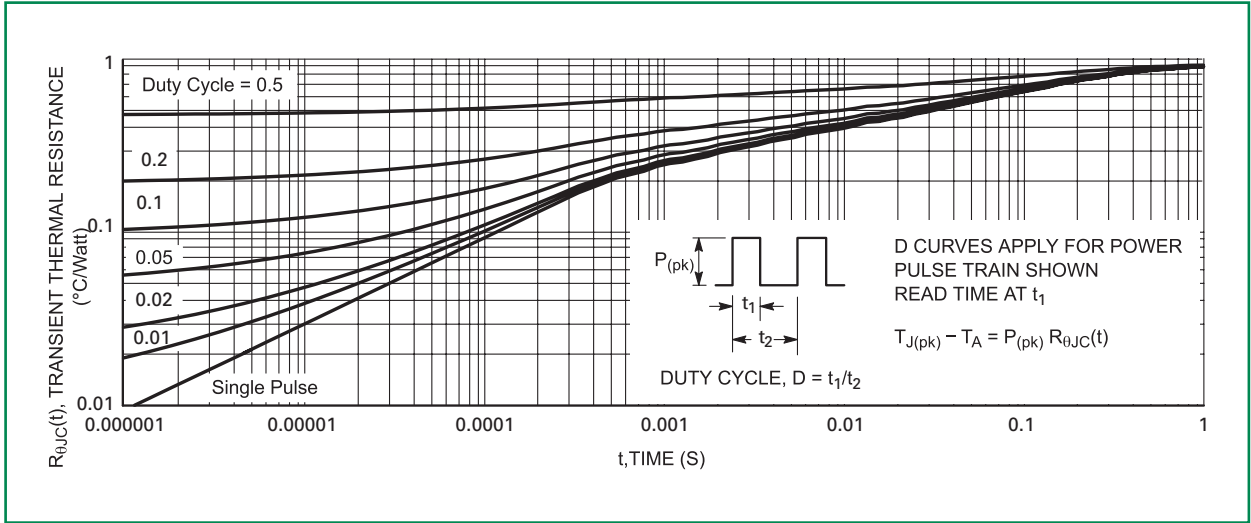
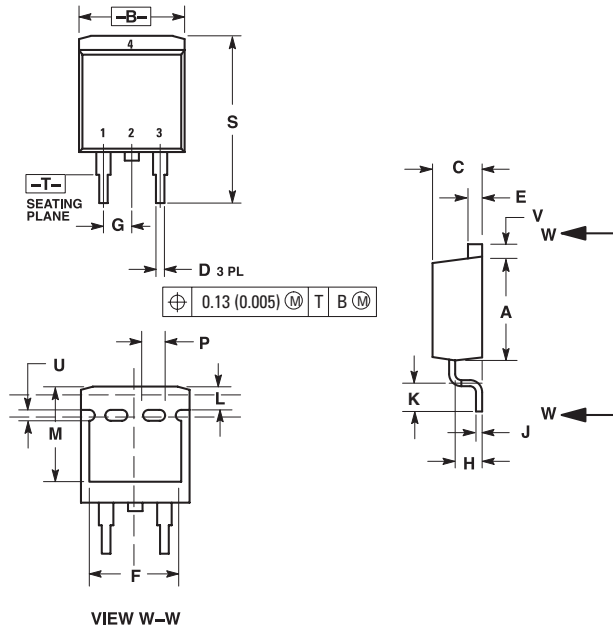


Figure 13. Minimum Pad Transient Thermal Resistance (Non-normalized Junction-to-Ambient)



Dimensions

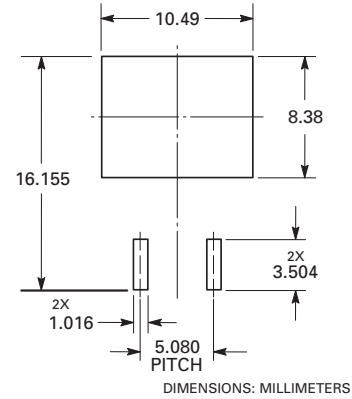


Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

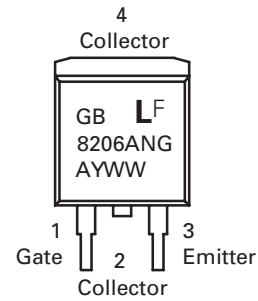
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

Soldering Footprint



Part Marking System



GB8206AN = Device Code

- A= Assembly Location
- Y= Year
- WW = Work Week
- G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGB8206ANT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NGB8206ANTF4G		700 / Tape & Reel
NGB8206ANSL3G		50 Units / Rail

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- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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